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Applicant: Toshiki Makimoto, et al.
 Serial No.: 10/516,380
 Filing Date: November 30, 2004
 For: P-TYPE NITRIDE SEMICONDUCTOR STRUCTURE AND BIPOLAR TRANSISTOR



Sheet 1 of 3
 Confirmation No.: 2860
 Att'y Docket No.: 14321.63
 Art Unit: 2818

INFORMATION DISCLOSURE CITATIONS MADE BY APPLICANT

U.S. Patent Documents

Examiner Initial*	Document Number	Issue Date	Name
THN 1	2002/0146855 A1	10/10/2002	Goto et al.

Foreign Patent Documents

Examiner Initial*	Document Number	Publication Date	Country or Patent Office	Translation
THN 2	5-175225	7/13/1993	Japan	No
THN 3	5-291282	11/5/1993	Japan	No
THN 4	7-245316	9/19/1995	Japan	No
THN 5	2003-007998	1/10/2003	Japan	No
THN 6	2002-305204	10/18/2002	Japan	No
THN 7	10-065216	03/06/2002	Japan	No
THN 8	11-150296	06/02/1999	Japan	No

Other Documents

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THN 9 K. Kumakura, T. Makimoto and N. Kobayashi, *Low-Resistance Nonalloyed Ohmic Contact to p-type GaN Using Strained InGaN Contact Layer*, Applied Physics Letters, Vol. 79, No. 16, pp 2588-2590 (2001).

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Date Considered:

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12/16/2006

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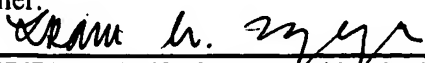
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- THN 10 T. Makimoto, et al., *Reduced Damage Of Electron Cyclotron Resonance Etching By In Doping Into p-GaN*, Journal of Crystal Growth 221, pp. 350-355 (2000).
- THN 11 T. Makimoto, et al., *High Current Gains Obtained by InGaN/GaN Double Heterojunction Bipolar Transistors*, phys. stat. sol. (a) 188, No. 1, pp. 183-186, (2001).
- THN 12 L.S. McCarthy, et al., *AlGaIn/GaN Heterojunction Bipolar Transistor*, IEEE Electron Device Letters, Vol. 20, No. 6, pp. 277-270 (1999).
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- THN 14 K.P. Lee, et al., *Self-Aligned Process for Emitter- and Base-Regrowth GaN HBTs and BJTs*, Solid-State Electronics 45, pp. 243-247 (2001),
- THN 15 T. Makimoto et al., *High Current Gain of 3000 for GaN/InGaIn HBTs with a Regrown Base Layer*, Technical Report of IEICE. ED2003-25 CPM2003-24 SDM2003-25 (2003-5), pp. 49-52.
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- THN 17 T. Makimoto et al., *High Current Gain (>2000) and Reduced Common-emitter Offset Voltage of GaN/InGaIn Double Heterojunction Bipolar Transistors*, Conference Digest of 61st Device Research Conference, pp. 23-24, June 23-25, 2003.
- THN 18 T. Makimoto et al., *High Current Gain (>2000) of GaN/InGaIn double Heterojunction Bipolar Transistors Using Base Regrowth of p-InGaIn*, Applied Physics Letters, Vol. 83, No. 5, pp. 1035-1037 (2003).

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